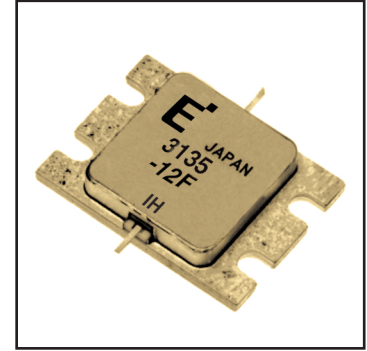


### FEATURES

- High Output Power:  $P_{1dB} = 41.5\text{dBm}$  (Typ.)
- High Gain:  $G_{1dB} = 11.5\text{dB}$  (Typ.)
- High PAE:  $\eta_{add} = 40\%$  (Typ.)
- Low  $IM_3 = -45\text{dBc}$  @  $P_o = 30.5\text{dBm}$
- Broad Band: 3.1 ~ 3.5GHz
- Impedance Matched  $Z_{in}/Z_{out} = 50\Omega$
- Hermetically Sealed Package



### DESCRIPTION

The FLM3135-12F is a power GaAs FET that is internally matched for standard communication bands to provide optimum power and gain in a 50 ohm system.

Eudyna's stringent Quality Assurance Program assures the highest reliability and consistent performance.

### ABSOLUTE MAXIMUM RATING (Ambient Temperature $T_a=25^\circ\text{C}$ )

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	$V_{DS}$		15	V
Gate-Source Voltage	$V_{GS}$		-5	V
Total Power Dissipation	$P_T$	$T_c = 25^\circ\text{C}$	57.6	W
Storage Temperature	$T_{stg}$		-65 to +175	$^\circ\text{C}$
Channel Temperature	$T_{ch}$		175	$^\circ\text{C}$

Fujitsu recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage ( $V_{DS}$ ) should not exceed 10 volts.
2. The forward and reverse gate currents should not exceed 32.0 and -5.6 mA respectively with gate resistance of 50 $\Omega$ .

### ELECTRICAL CHARACTERISTICS (Ambient Temperature $T_a=25^\circ\text{C}$ )

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Saturated Drain Current	$I_{DSS}$	$V_{DS} = 5\text{V}, V_{GS} = 0\text{V}$	-	5800	8700	mA
Transconductance	$g_m$	$V_{DS} = 5\text{V}, I_{DS} = 3400\text{mA}$	-	2900	-	mS
Pinch-off Voltage	$V_p$	$V_{DS} = 5\text{V}, I_{DS} = 300\text{mA}$	-1.0	-2.0	-3.5	V
Gate Source Breakdown Voltage	$V_{GSO}$	$I_{GS} = -300\mu\text{A}$	-5.0	-	-	V
Output Power at 1dB G.C.P.	$P_{1dB}$	$V_{DS} = 10\text{V},$ $I_{DS} = 0.55 I_{DSS}$ (Typ.), $f = 3.1 \sim 3.5 \text{GHz},$ $Z_S = Z_L = 50 \text{ohm}$	40.5	41.5	-	dBm
Power Gain at 1dB G.C.P.	$G_{1dB}$		10.5	11.5	-	dB
Drain Current	$I_{dsr}$		-	3250	3800	mA
Power-added Efficiency	$\eta_{add}$		-	40	-	%
Gain Flatness	$\Delta G$		-	-	$\pm 0.6$	dB
3rd Order Intermodulation Distortion	$IM_3$		$f = 3.5 \text{GHz}, \Delta f = 10 \text{MHz}$ 2-Tone Test $P_{out} = 30.5\text{dBm}$ S.C.L.	-42	-45	-
Thermal Resistance	$R_{th}$	Channel to Case	-	2.3	2.6	$^\circ\text{C}/\text{W}$
Channel Temperature Rise	$\Delta T_{ch}$	$10\text{V} \times I_{dsr} \times R_{th}$	-	-	80	$^\circ\text{C}$

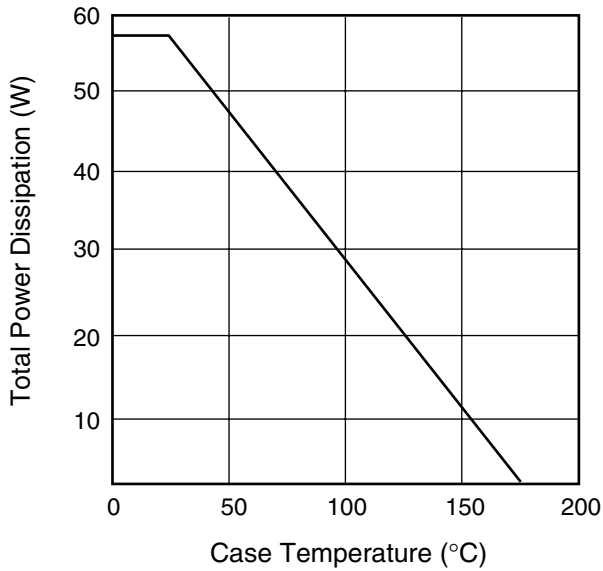
CASE STYLE: IK

G.C.P.: Gain Compression Point, S.C.L.: Single Carrier Level

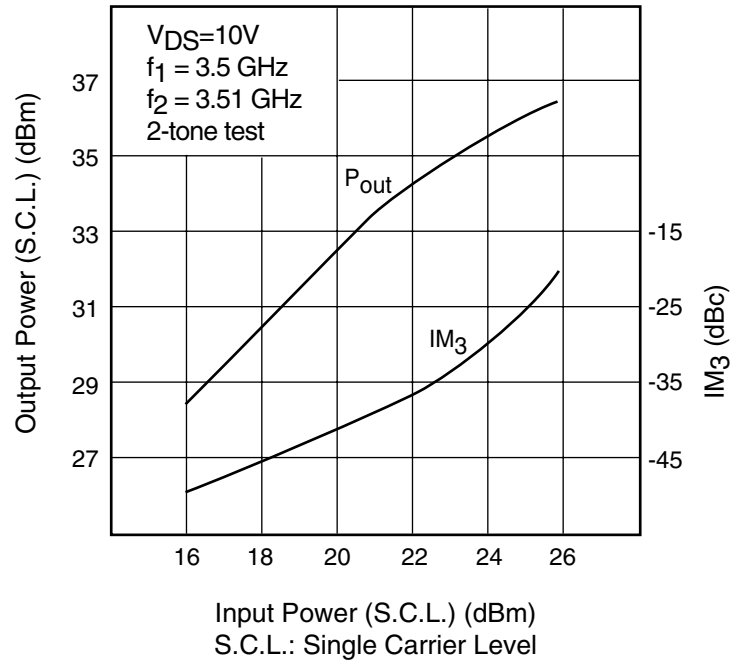
# FLM3135-12F

## C-Band Internally Matched FET

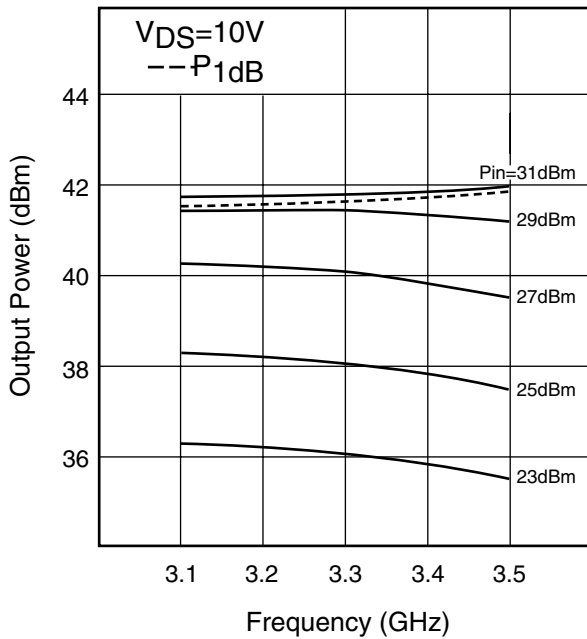
**POWER DERATING CURVE**



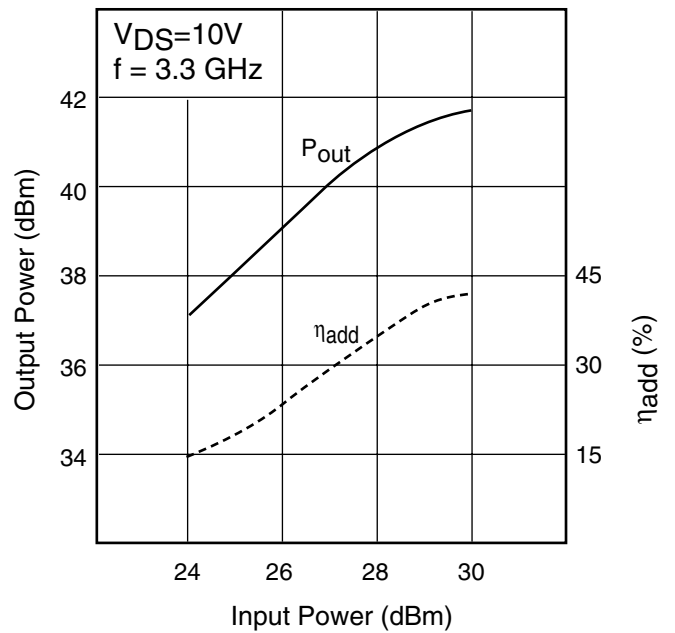
**OUTPUT POWER & IM<sub>3</sub> vs. INPUT POWER**

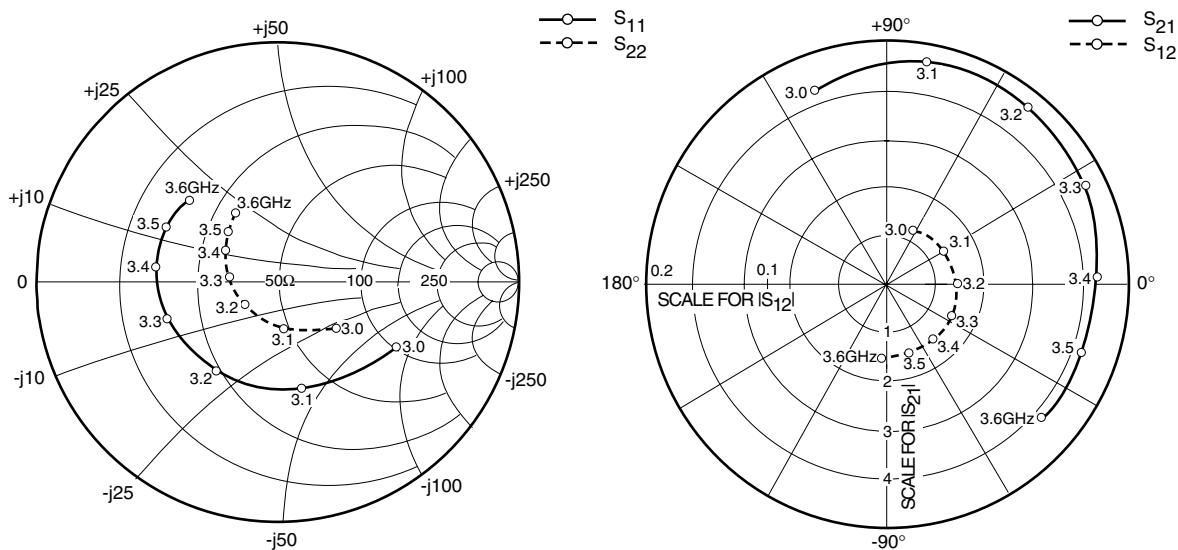


**OUTPUT POWER vs. FREQUENCY**



**OUTPUT POWER vs. INPUT POWER**





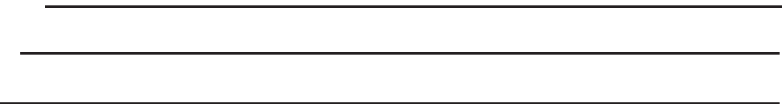
### S-PARAMETERS

$V_{DS} = 10V, I_{DS} = 3400mA$

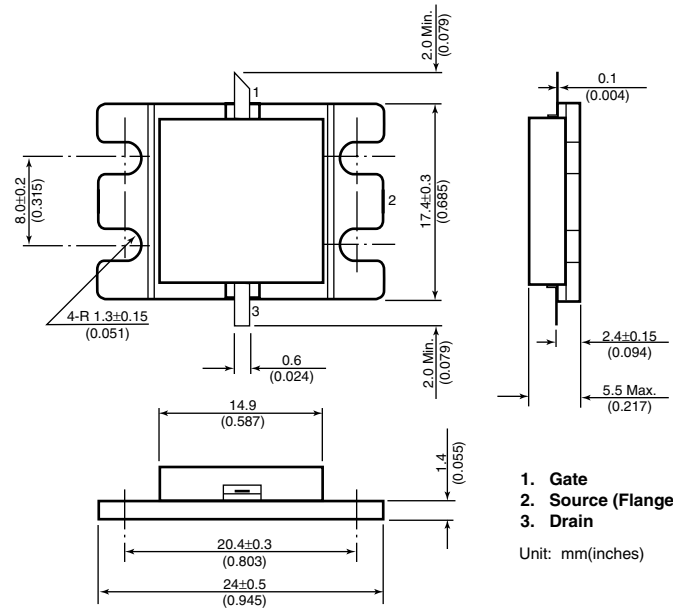
FREQUENCY (MHZ)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
3000	.560	-29.4	4.236	110.6	.049	63.4	.310	-37.8
3100	.462	-77.4	4.622	80.1	.056	30.3	.191	-84.3
3200	.450	-124.9	4.657	51.1	.059	0.0	.165	-146.9
3300	.481	-160.8	4.507	25.1	.059	-27.0	.206	174.4
3400	.510	173.2	4.346	1.7	.060	-50.4	.258	149.8
3500	.521	153.7	4.232	-20.0	.060	-73.7	.298	135.3
3600	.505	137.2	4.223	-40.9	.062	-94.6	.341	121.8

# FLM3135-12F

## C-Band Internally Matched FET



### Case Style "IK" Metal-Ceramic Hermetic Package



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#### CAUTION

Eudyna Devices Inc. products contain **gallium arsenide (GaAs)** which can be hazardous to the human body and the environment. For safety, observe the following procedures:

- Do not put this product into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.

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